

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05004	3	1 of 1

TYPE:6PT1002N1T

CHIP SIZE	1.1 * 1.1mm
WAFER SIZE	6inch
POSSIBLE DIE PER WAFER	12,650pcs

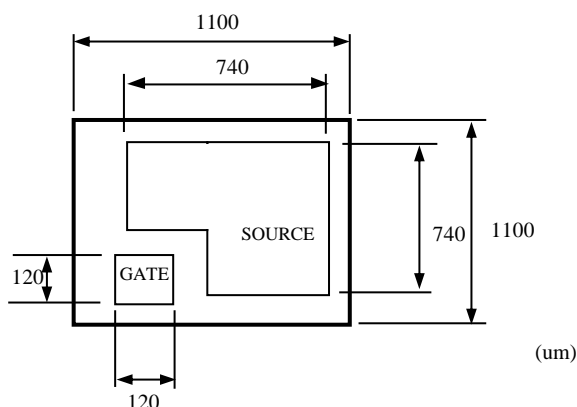
Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	IGSS			±1	uA	VGS=±8V VDS=0V
2	IDSS			500	nA	VDS=20V VGS=0V
3	BVDSS	23			V	ID=100μA
4	VTH	0.53		1	V	ID=1mA VDS=10V
5	RDS(on)1		27	40	mΩ	ID=2.0A VGS=4.5V
6	RDS(on)2		35	50	mΩ	ID=2.0A VGS=2.5V
6	RDS(on)3		70	110	mΩ	ID=0.5A VGS=1.8V
7	VSD		0.85	1.1	V	I=2A VGS=0V
8	Yfs		4		S	Vds=10V Id=0.5A

※ Built-in ZD between Gate and Source.



NOTE: